



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re Patent Application of )  
Taiji NODA et al. ) Group Art Unit: 2814  
Serial No. 09/662,358 ) Examiner: Anh D. MAI  
Filed: September 15, 2000 )  
For: SEMICONDUCTOR DEVICE AND )  
METHOD FOR FABRICATING )  
THE SAME )

**RESPONSE TO NOTICE OF NON-COMPLIANT AMENDMENT**

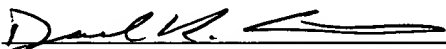
Commissioner for Patents  
Washington, D.C. 20231

September 5, 2002

Sir:

In response to the Notice of Non-Compliant Amendment (37 CFR 1.121) mailed August 27, 2002, Applicants respectfully submit the completed Amendment to include the clean copy of amendments to the claims, together with the marked-up version of the amended claims as an attachment.

Respectfully submitted,

  
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AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Examiner's non-final Office Action mailed February 11, 2002, the due date for which having been extended three months to August 26, 2002, please consider the following amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please cancel claims 16-19 without disclaimer or prejudice to the subject matter disclosed therein.

Please amend the claims as follows:

6. (Amended) A method for fabricating a semiconductor device that includes an extended high-concentration dopant diffused layer of a first conductivity and a pocket dopant diffused layer of a second conductivity, comprising:

a first step of forming a gate electrode over a semiconductor region with a gate insulating film interposed therebetween;

a second step of implanting heavy ions into the semiconductor region using the gate electrode as a mask, thereby forming a first ion implanted layer of the second conductivity, at least upper part of which is an amorphous layer;